IN THE SPECIFICATION

Please delete the paragraph at page 14, lines 22-26, in its entirety.

Please amend the paragraph at page 14, line 27 to page 16, line 16, as follows:

~~The above object of this invention can be attained by~~ According to an aspect of the present invention, there is provided a solid-state imaging device ~~comprising~~ that includes an imaging area having unit cells arranged in a two-dimensional fashion on a semiconductor substrate, each of the unit cells including first and second photoelectric conversion/storage sections for photoelectrically converting incident light and storing charges thus generated, first and second charge readout circuits for transferring charges stored in the first and second photoelectric conversion/storage sections to a common charge detecting section, a potential detecting circuit for detecting charges transferred to the charge detecting section, generating a potential corresponding to an amount of charges and transmitting the potential to a corresponding one of vertical signal lines, a reset circuit for discharging the charge transferred to the charge detecting section, and an address circuit for selectively activating the potential detecting circuit; a vertical driving circuit provided in correspondence to each pixel row of the imaging area, for driving the first and second charge readout circuits, reset circuit and address circuit of each of the unit cells at preset timings; signal processing circuits respectively attached to the vertical signal lines which are respectively provided for columns of the unit cells, for performing required signal processes; a horizontal driving circuit for scanning outputs of the signal processing circuits in a horizontal direction at preset timings to detect the same; and an output circuit for outputting output signals of the signal processing circuits detected by the scanning operation by the horizontal driving circuit; wherein the solid-state imaging device has a first operation mode in which the first and second charge readout circuits are driven at substantially the same timing by the vertical driving circuit, the

charges stored in the first and second photoelectric conversion/storage sections are transferred to and added together in the charge detecting section, and the potential detecting circuit detects the added charges, generates and transmits a potential corresponding to the amount of the detected charges to the vertical signal line, and outputs the potential from the output circuit via the signal processing circuits.

Please delete the paragraph at page 16, lines 17-26, in its entirety.

Please delete the paragraphs at page 16, line 27 to page 20, line 2, in their entireties.

Please amend the paragraph at page 20, line 3 to page 21, line 20, as follows:

~~The above object of this invention can be attained by~~ According to another aspect of the present invention, there is provided a readout method of a solid-state imaging device which includes an imaging area having unit cells arranged in a two-dimensional fashion on a semiconductor substrate, each of the unit cells including first and second photoelectric conversion/storage sections for photoelectrically converting incident light and storing charges thus generated, first and second charge readout circuits for transferring charges stored in the first and second photoelectric conversion/storage sections to a common charge detecting section, a potential detecting circuit for detecting charges transferred to the charge detecting section, generating a potential corresponding to an amount of detected charges and transmitting the potential to a corresponding one of vertical signal lines, a reset circuit for discharging the charges transferred to the charge detecting section, and an address circuit for selectively activating the potential detecting circuit, a vertical driving circuit provided in correspondence to each pixel row of the imaging area, for driving the first and second charge readout circuits, reset circuit and address circuit of each of the unit cells at preset timings,

signal processing circuits respectively attached to the vertical signal lines which are respectively provided for columns of the unit cells, for performing required signal processes; a horizontal driving circuit for scanning outputs of the signal processing circuits in a horizontal direction at preset timings to detect the same, and an output circuit for outputting output signals of the signal processing circuits detected by the scanning operation by the horizontal driving circuit, ~~comprising the steps of~~ the method including driving the first and second charge readout circuits at substantially the same timing by use of the vertical driving circuit; transferring the charges stored in the first and second photoelectric conversion/storage sections to the charge detecting section and adding the charges together; detecting the added charges by use of the potential detecting circuit; generating a potential corresponding to an amount of the detected charges and transmitting the potential to the vertical signal line; and outputting the potential from the output circuit via the signal processing circuits.

Please delete the paragraphs at page 21, line 21 to page 25, line 16, in their entireties.

Please delete the paragraph at page 25, lines 18-24, in its entirety.

Please amend the paragraph at page 49, lines 7-10, as follows:

As described above, according to one aspect of this invention, a solid-state imaging device capable of suppressing a lowering in the S/N ratio when the high-speed driving operation is effected can be attained.